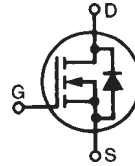


TrenchT2™ Power MOSFET

IXTA170N075T2 IXTP170N075T2

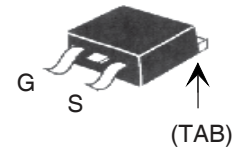
$V_{DSS} = 75V$
 $I_{D25} = 170A$
 $R_{DS(on)} \leq 5.4m\Omega$

N-Channel Enhancement Mode
Avalanche Rated

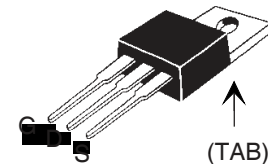


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $175^\circ C$	75	V
V_{DGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$	75	V
V_{GSM}	Transient	± 20	V
I_{D25}	$T_C = 25^\circ C$	170	A
I_{LRMS}	Lead Current Limit, RMS	75	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	510	A
I_{AR}	$T_C = 25^\circ C$	85	A
E_{AS}	$T_C = 25^\circ C$	600	mJ
P_D	$T_C = 25^\circ C$	360	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	1.6mm (0.062in.) from case for 10s	300	$^\circ C$
T_{sold}	Plastic body for 10 seconds	260	$^\circ C$
M_d	Mounting torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g

TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
 S = Source TAB = Drain

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- $175^\circ C$ Operating Temperature
- High current handling capability
- ROHS Compliant
- High performance Trench Technology for extremely low $R_{DS(on)}$

Advantages

- Easy to mount
- Space savings
- High power density
- Synchronous

Applications

- Synchronous Buck Converters
- High Current Switching Power Supplies
- Battery Powered Electric Motors
- Resonant-mode power supplies
- Electronics Ballast Application
- Class D Audio Amplifiers

Symbol	Test Conditions ($T_J = 25^\circ C$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	75		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0V$ $T_J = 150^\circ C$			100 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 50A$, Notes 1, 2			5.4 $m\Omega$

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 60\text{A}$, Note 1	40	70	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		6860	pF
C_{oss}			810	pF
C_{rss}			148	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 3.3\Omega$ (External)		19	ns
t_r			11	ns
$t_{d(off)}$			25	ns
t_f			19	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		109	nC
Q_{gs}			37	nC
Q_{gd}			25	nC
R_{thJC}			0.42	$^\circ\text{C/W}$
R_{thCH}	TO-220	0.50		$^\circ\text{C/W}$

Source-Drain Diode

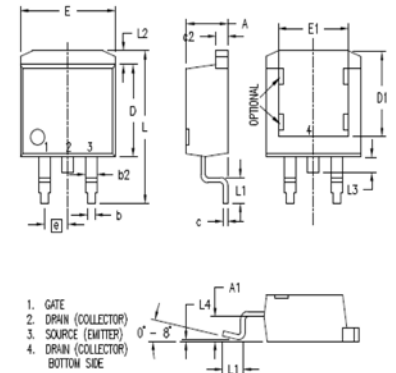
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			170 A
I_{SM}	Repetitive, Pulse width limited by T_{JM}			680 A
V_{SD}	$I_F = 50\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.0 V
t_{rr}	$I_F = 85\text{A}$, $V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 37\text{V}$		63	ns
I_{RM}			4.8	A
Q_{RM}			150	nC

- Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

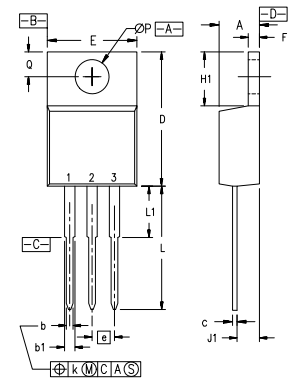
TO-263 (IXTA) Outline



- GATE
 - DRAIN (COLLECTOR)
 - SOURCE (EMITTER)
 - DRAIN (COLLECTOR)
- BOTTOM SIDE

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-220 (IXTP) Outline



- Pins: 1 - Gate
2 - Drain
3 - Source
4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
L2	.139	.161	3.53	4.08
L3	.100	.125	2.54	3.18

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics
@ 25°C

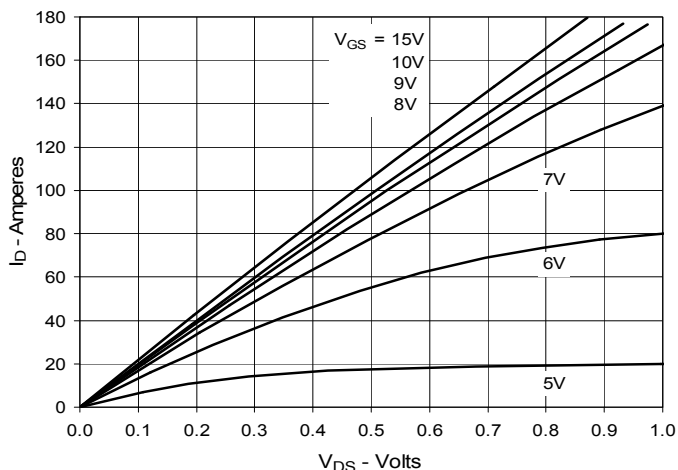


Fig. 2. Extended Output Characteristics
@ 25°C

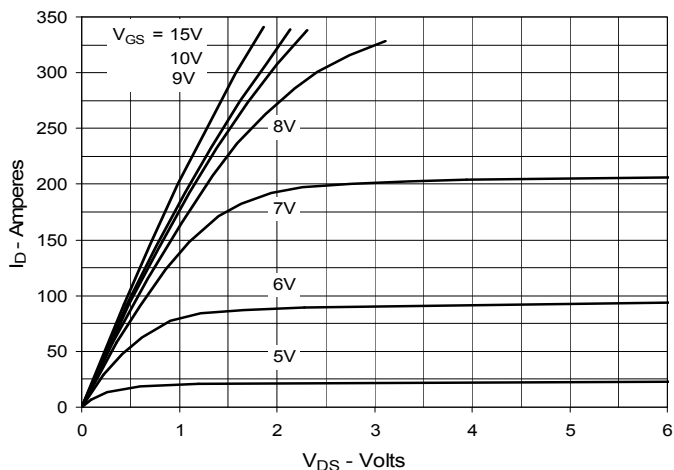


Fig. 3. Output Characteristics
@ 150°C

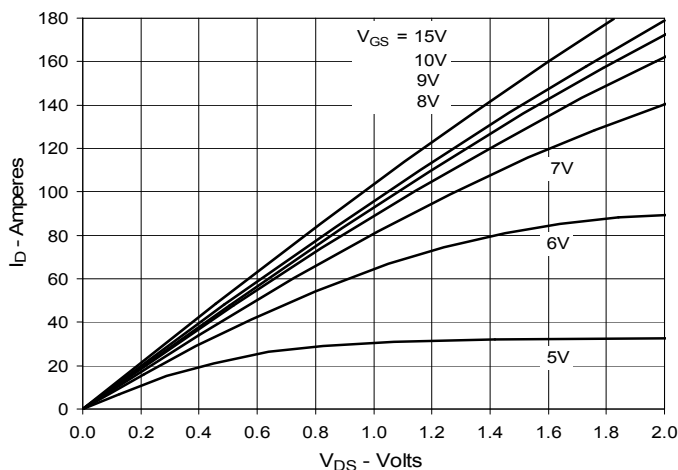


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 85A$ Value vs. Junction Temperature

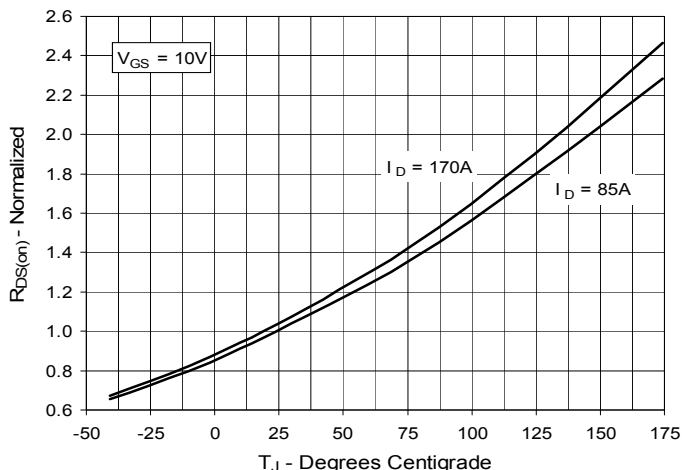


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 85A$ Value vs. Drain Current

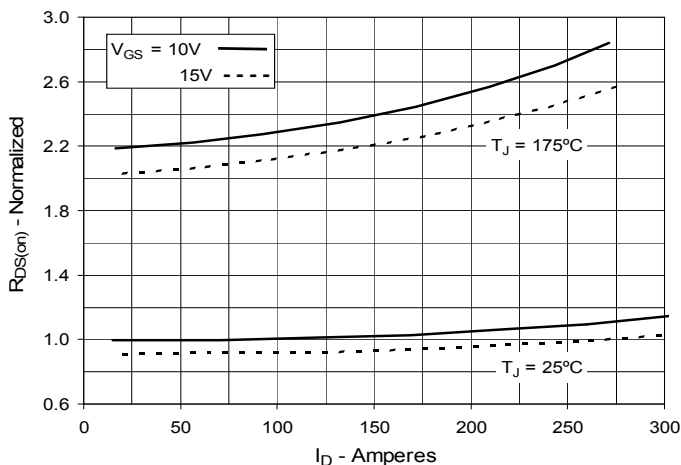


Fig. 6. Drain Current vs. Case Temperature

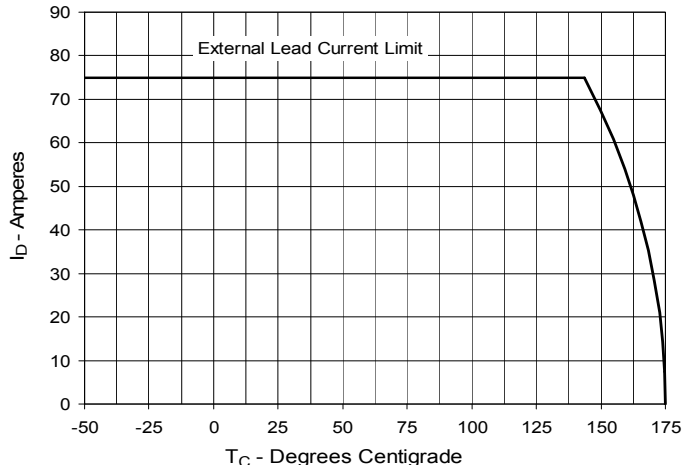


Fig. 7. Input Admittance

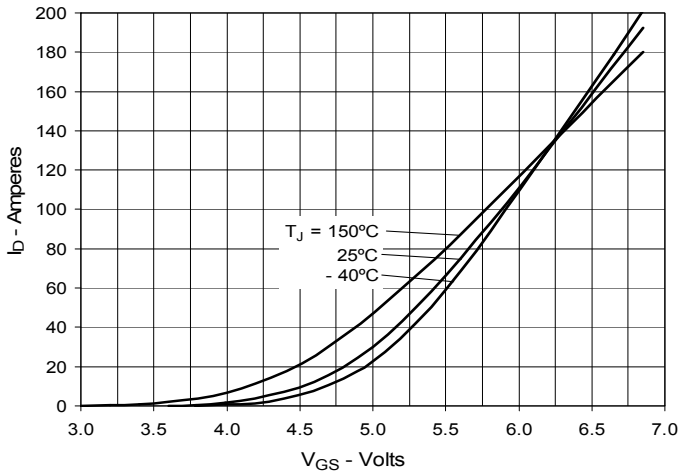


Fig. 8. Transconductance

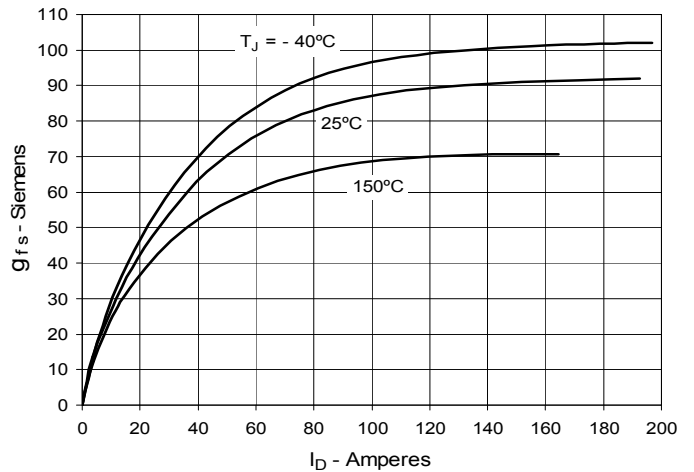


Fig. 9. Forward Voltage Drop of Intrinsic Diode

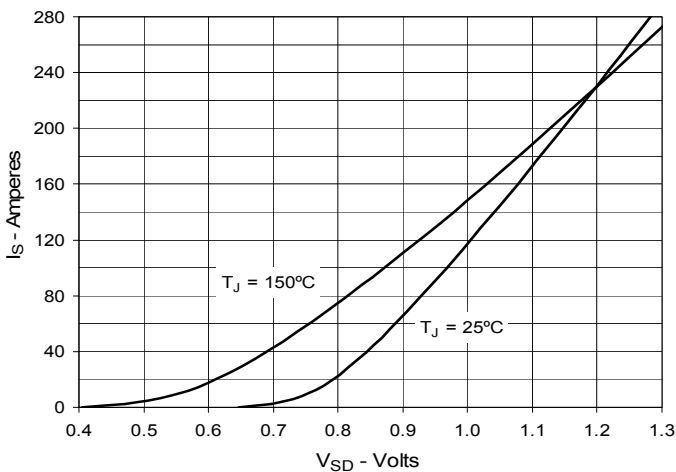


Fig. 10. Gate Charge

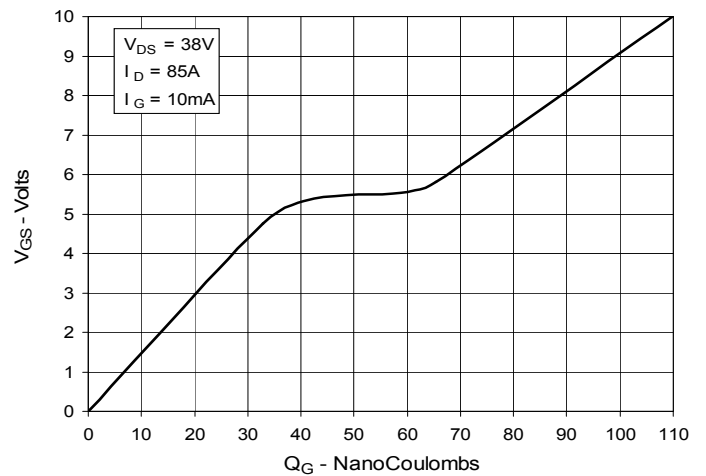


Fig. 11. Capacitance

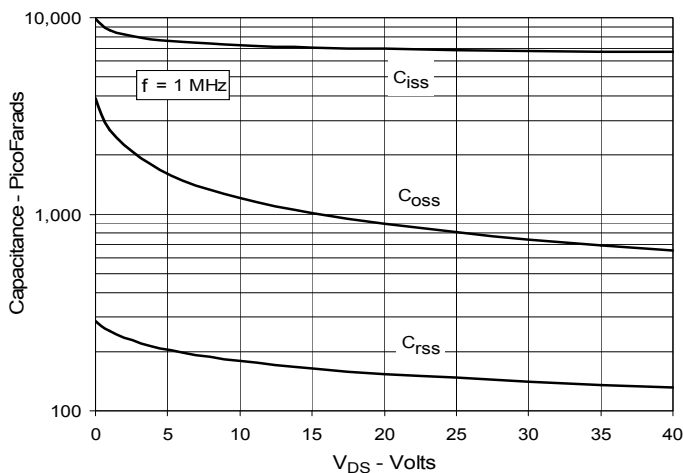
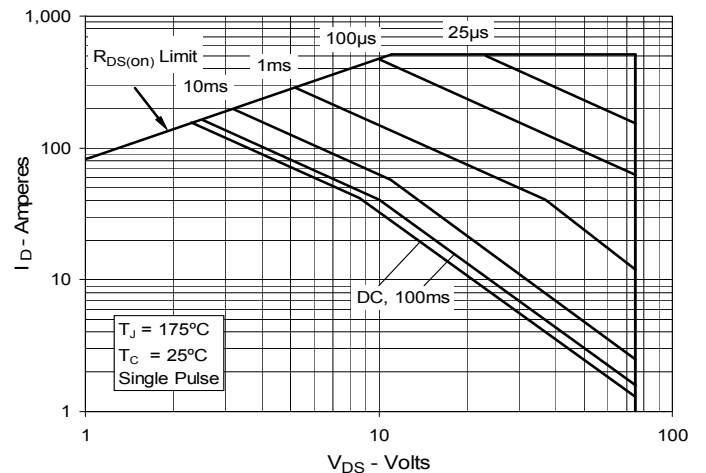
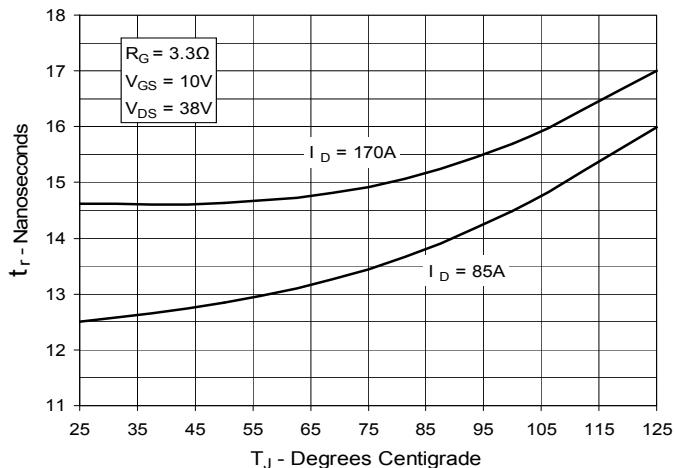


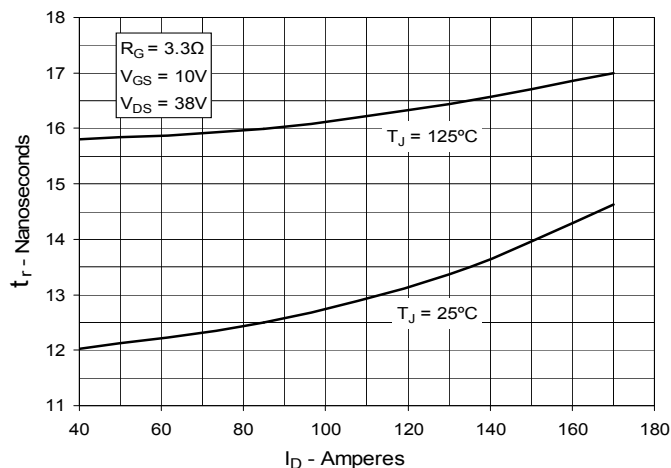
Fig. 12. Forward-Bias Safe Operating Area



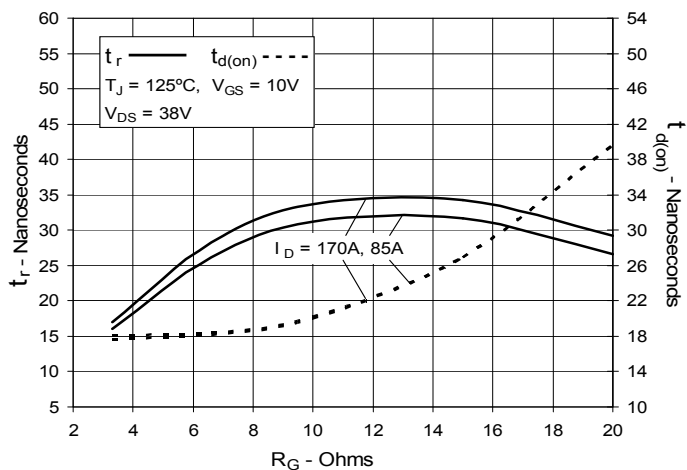
**Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature**



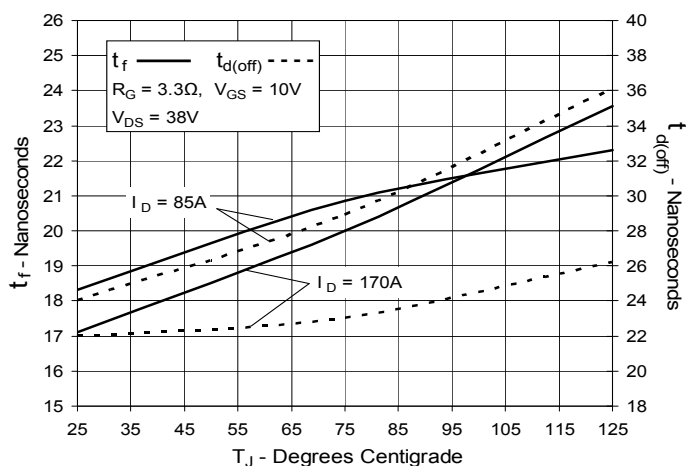
**Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current**



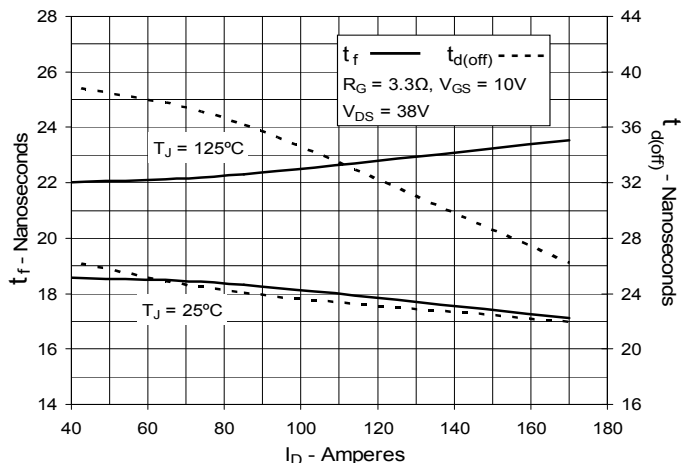
**Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance**

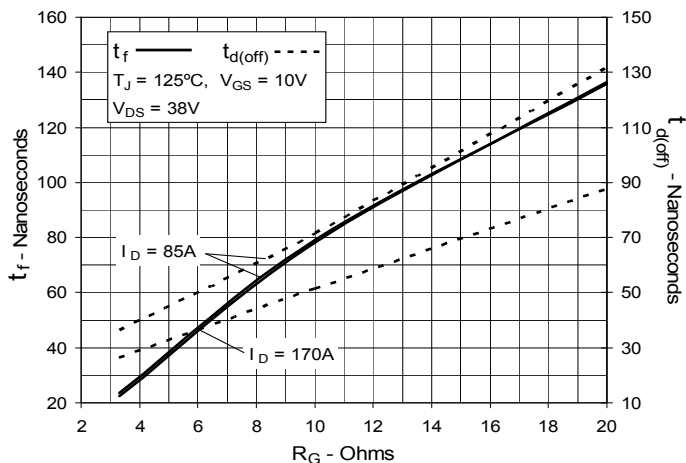


Fig. 19. Maximum Transient Thermal Impedance

